

**Silicon PNP Power Transistors**

**2SB1272**

**DESCRIPTION**

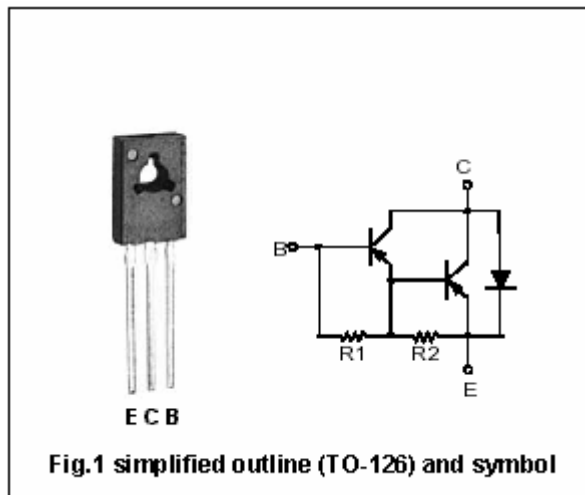
- With TO-126 package
- DARLINGTON
- High DC current gain

**APPLICATIONS**

- For low frequency power amplifier applications

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



**Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CB0</sub>	Collector-base voltage	Open emitter	-100	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-100	V
V <sub>EBO</sub>	Emitter -base voltage	Open collector	-7	V
I <sub>C</sub>	Collector current		-2	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	10	W
T <sub>J</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## 2SB1272

## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA; I <sub>B</sub> =0	-100			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-1mA; I <sub>E</sub> =0	-100			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-5mA; I <sub>C</sub> =0	-7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-2A; I <sub>B</sub> =-2mA			-2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-2A; I <sub>B</sub> =-2mA			-2.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =100V; I <sub>E</sub> =0			-0.1	mA
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =100V; I <sub>B</sub> =0			-0.5	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-7V; I <sub>C</sub> =0			-5.0	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-2V	1000		10000	

PACKAGE OUTLINE

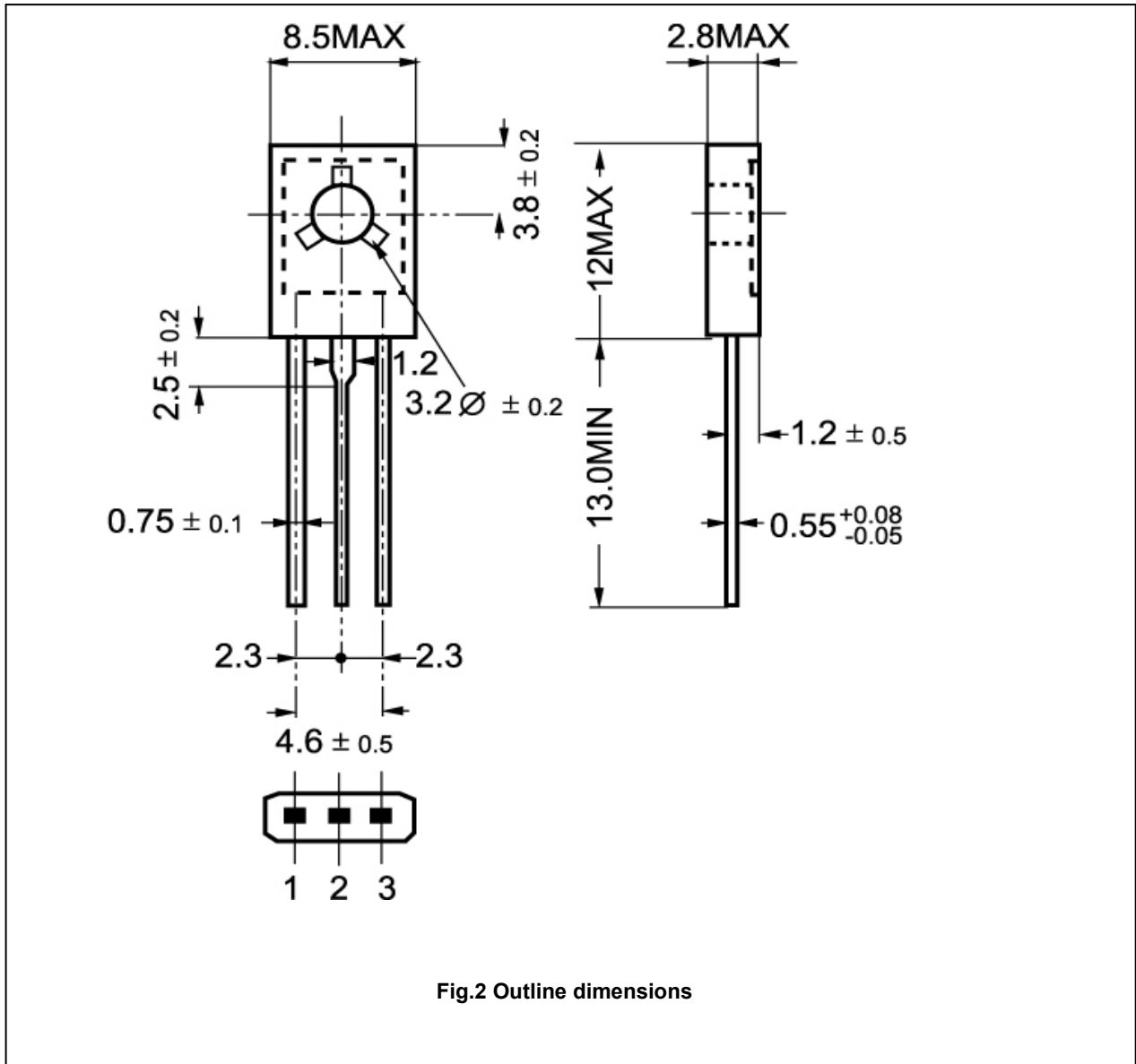


Fig.2 Outline dimensions